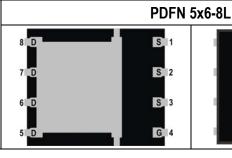


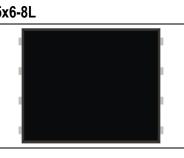
60V N-Channel Power MOSFET

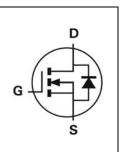
V_{DSS}, 60V

 $R_{DS(ON)}$, $10m\Omega$ (max.) @ $V_{GS}{=}10V$ $R_{DS(ON)}$, $13m\Omega$ (max.) @ $V_{GS}{=}4.5V$

 I_D , 46A







Description

The SG60N10Q uses advanced Trench technology and designs to provide excellent $R_{\text{DS}(\text{ON})}$ with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

Features

- Low On-Resistance
- Low Input Capacitance
- Low Miller Charge
- Low Input / Output Leakage
- · Pb-free lead plating; RoHS compliant

Applications

- Motor / Body Load Control
- Automotive Systems
- Load Switch
- DC-DC converters and Off-line UPS

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG60N10Q	Halogen-Free	PDFN 5x6-8L	Q	Tape & Reel	2,500

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parame	eter	Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	±20	V
Drain Current Continuous	Tc=25°C	l-	46	Α
Drain Current-Continuous	T _C =100°C	lo l	29	Α
Drain Current-Pulsed Note 1	·	I _{DM}	130	Α
Maximum Dawar Dissipation	T _C =25°C		32.9	W
Maximum Power Dissipation	T _C =100°C	P _D	13.2	W
Storage Temperature Range		T _{STG}	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	Reja	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	Rejc	Steady State	-	-	3.8	°C/W

1



60V N-Channel Power MOSFET

Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	1.2	1.7	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =9A	-	-	10	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _{DS} =5A	-	-	13	mΩ
Forward Transconductance	gfs	V _{DD} =10V, I _{DD} =6A	-	11	-	S

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	C _{iss}		-	1364	-	
Output Capacitance	Coss	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	113	-	pF
Reverse Transfer Capacitance	Crss		-	65	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	13.5	-	
Rise Time	tr	V_{GS} =10V, V_{DS} =30V, R_L =5 Ω ,	-	117	-	
Turn-Off Delay Time	T _{d(off)}	R _{GEN} =3Ω	-	49.8	-	ns
Fall Time	t _f		-	70	-	
Total Gate Charge	Qg		-	62	-	
Gate to Source Gate Charge	Qgs	V _{GS} =10V, V _{DS} =30V, I _D =10A	-	14.4	-	nC
Gate to Drain "Miller" Charge	Q_{gd}		-	16.5	-	
Gate resistance	Rg	V _{DS} =0V, V _{GS} =0V, f=1MHz	-	13.6	-	Ω

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =1A	-	-	1.3	V
Continuous Source Current	Is	120 A d1/dt-500 A/us	-	13	-	Α
Pulsed Source Current	Ism	l _F =20A, dl/dt=500A/μs	-	45	-	Α

Notes:

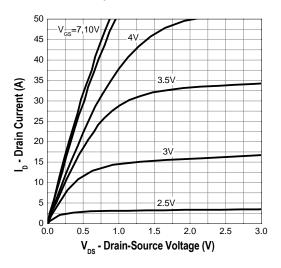
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Rejuc is guaranteed by design while Reja is determined by the user's board design. Reja shown below for single device operation on FR-4 in still air.



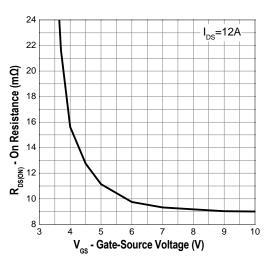
60V N-Channel Power MOSFET

Typical Operating Characteristics

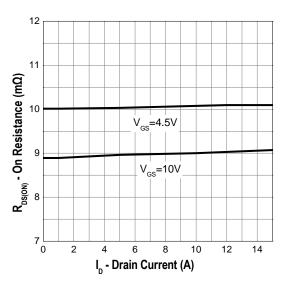
Output Characteristics



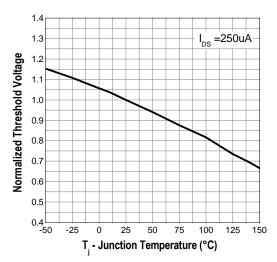
Gate-Source On Resistance



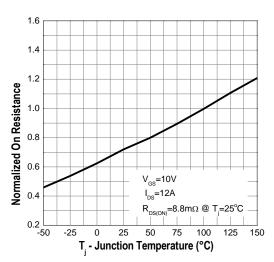
Drain-Source On Resistance



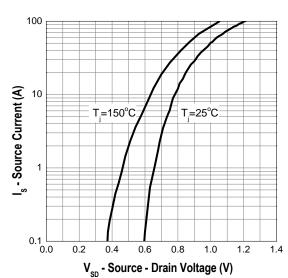
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward

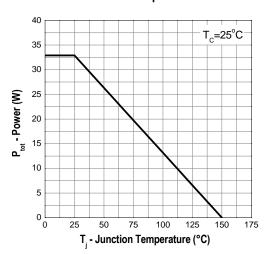




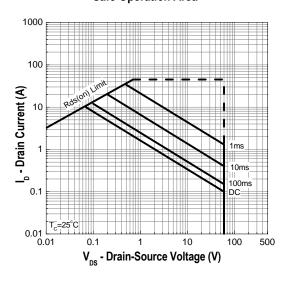
60V N-Channel Power MOSFET

Typical Operating Characteristics (Cont.)

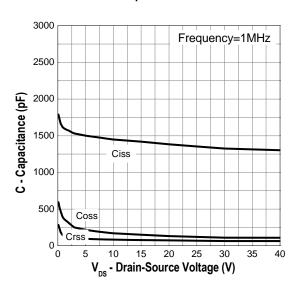
Power Dissipation



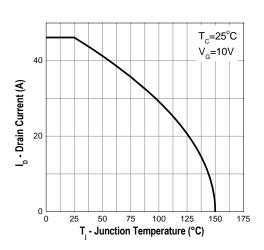
Safe Operation Area



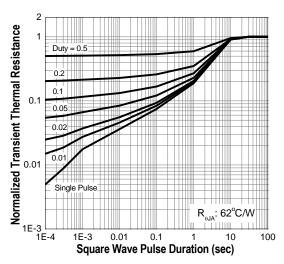
Capacitance



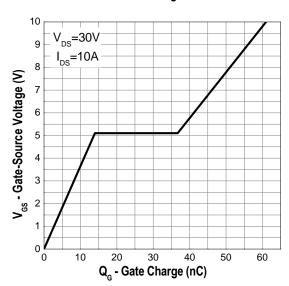
Drain Current



Transient Thermal Impedance



Gate Charge





SG60N10Q 60V N-Channel Power MOSFET

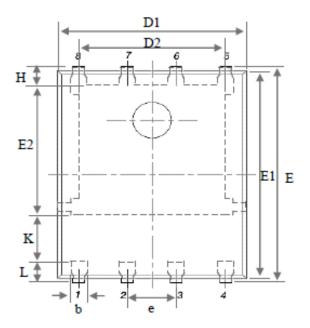
Marking Information

PDFN 5x6-8L (Q)	Marking Rule
Laser Marking	Line 1 : Device Name
	SG60N10Q
SG60N10Q	Line 2 : Date Code YYMMXXX
YYMMXXX	YY : Year Code MM : Month Code
Diagram	XXX : Serial Number

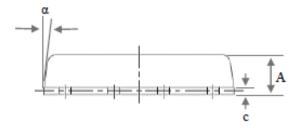




Package of Dimension



Symbol	Min	Nor	Max
Α	0.90	1.04	1.17
b	0.33	0.42	0.51
С	0.06	0.20	0.35
D1	4.80	5.10	5.40
D2	3.61	3.96	4.31
E	5.90	6.03	6.15
E1	5.65	5.75	5.85
E2	3.30	3.54	3.78
e		1.27 BSC	,
Н	0.38	0.50	0.61
Ĺ	0.38	0.55	0.71
L1	0.05	0.15	0.25



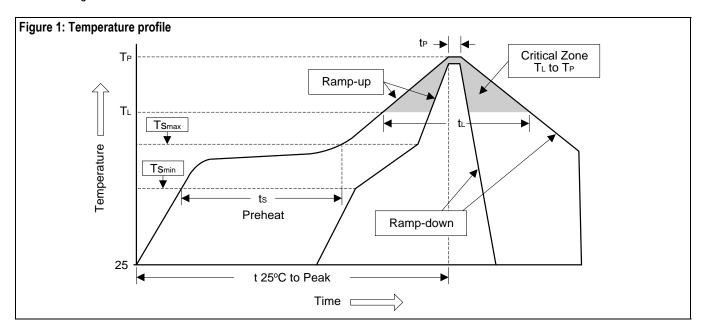
- 1. All dimension are in millimeters.
- 2. Dimension does not include burrs and mold flash/protrusions.



SG60N10Q 60V N-Channel Power MOSFET

Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t _∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 20 ooo	20 to 40 and
Temperature (t₂)	10 to 30 sec	20 to 40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



SG60N10Q 60V N-Channel Power MOSFET

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